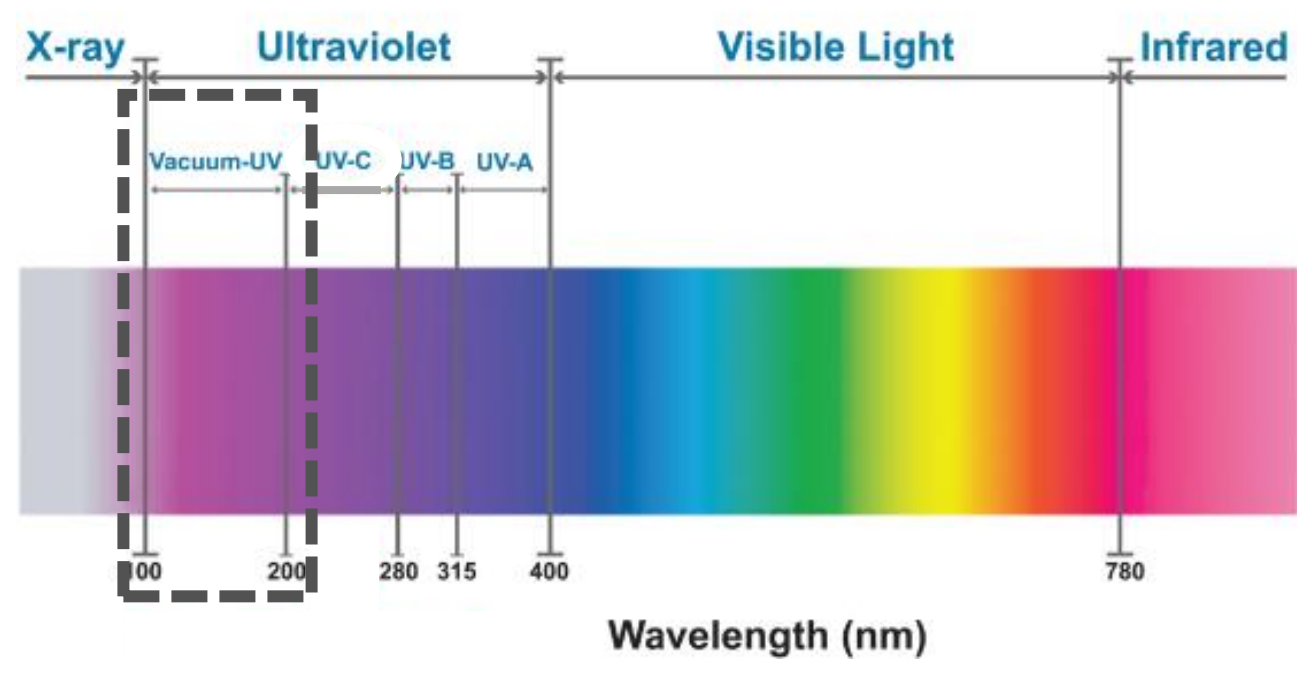


Glass-free SiPMs with Through Silicon Vias for VUV Light Detection

J. Dalmasson¹, L. Parellada-Monreal¹, F. Acerbi¹, A. Ficorella¹, A. Gola¹, S. Merzi¹, M. Ruzzarin¹, N. Zorzi¹ and G. Paternoster¹

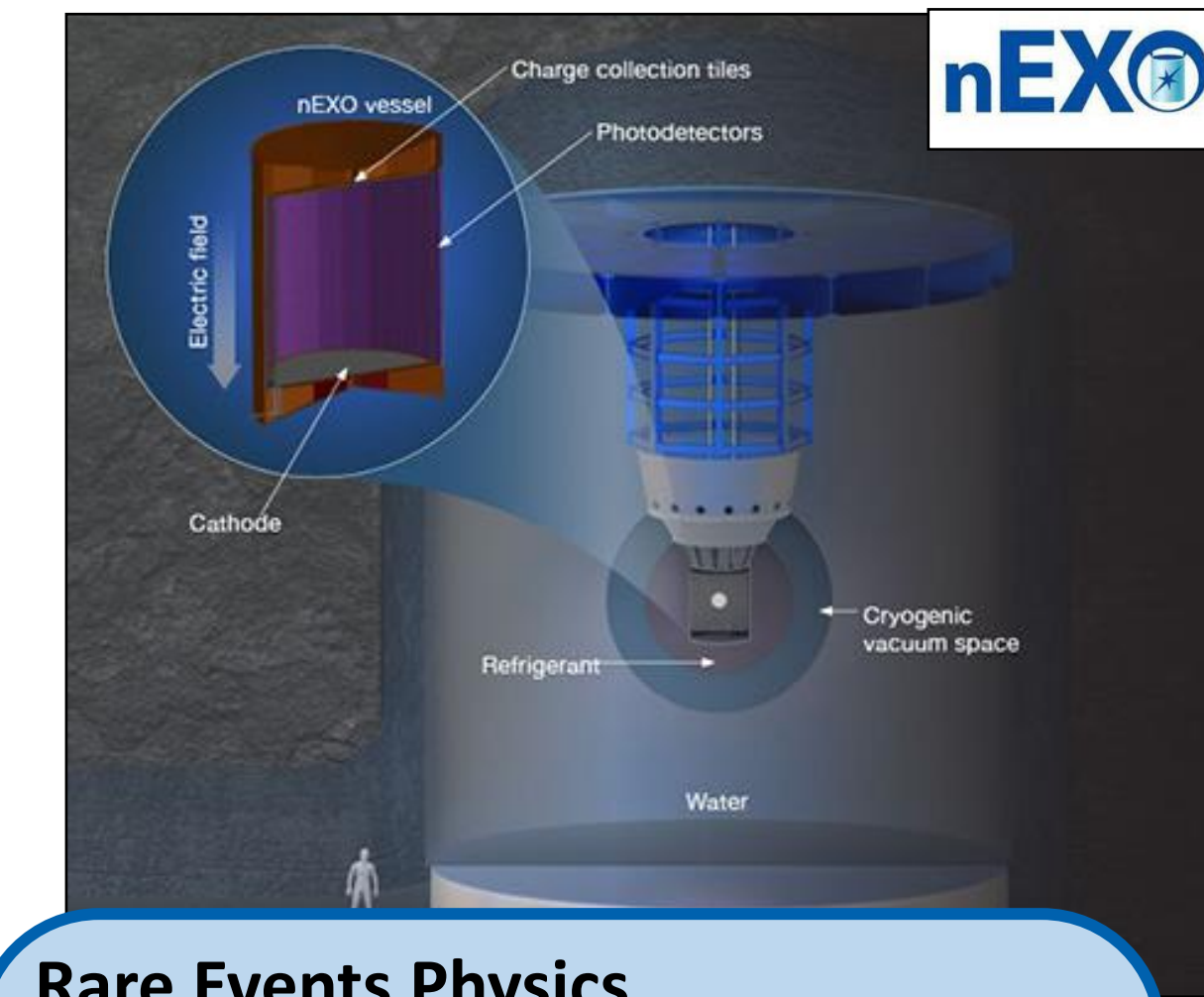
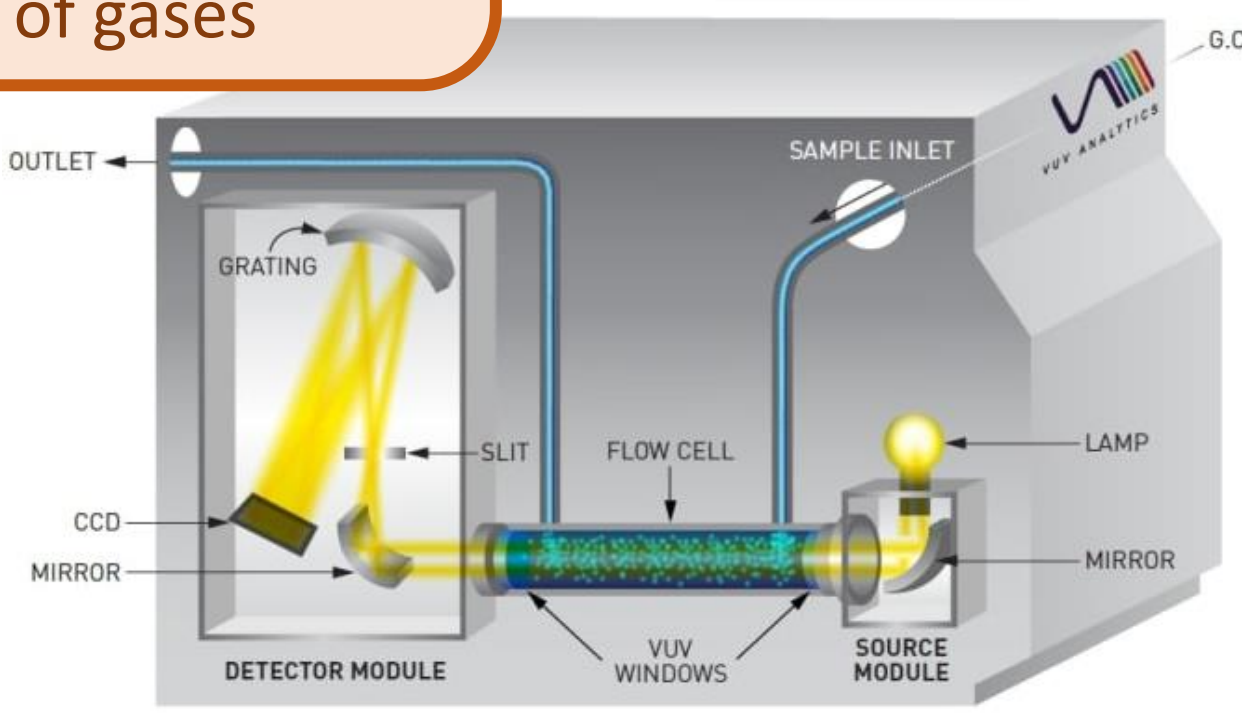
¹ Fondazione Bruno Kessler, via Sommarive 18, Trento, Italy

Application of VUV Detection



Industrial Gas Analysis

- Isomer identification
- Interaction with wide variety of gases

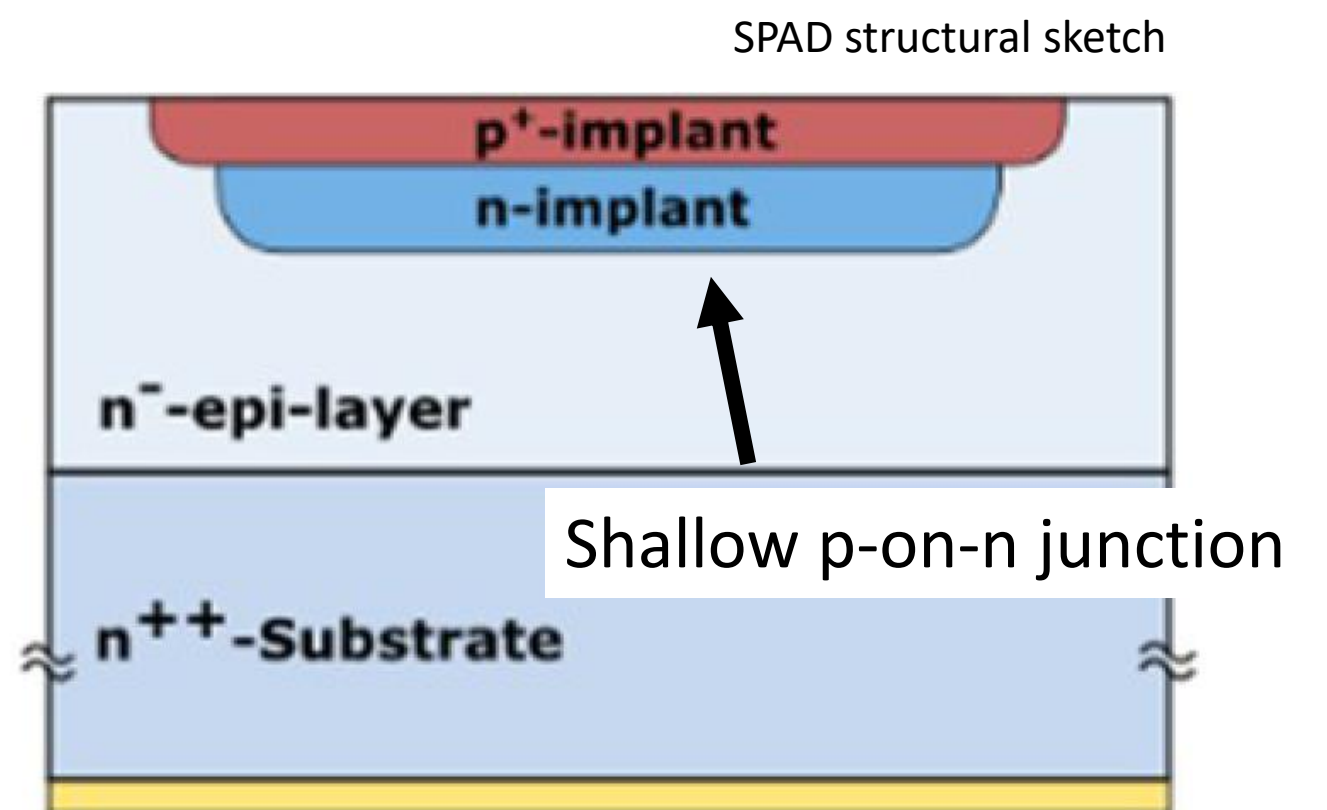
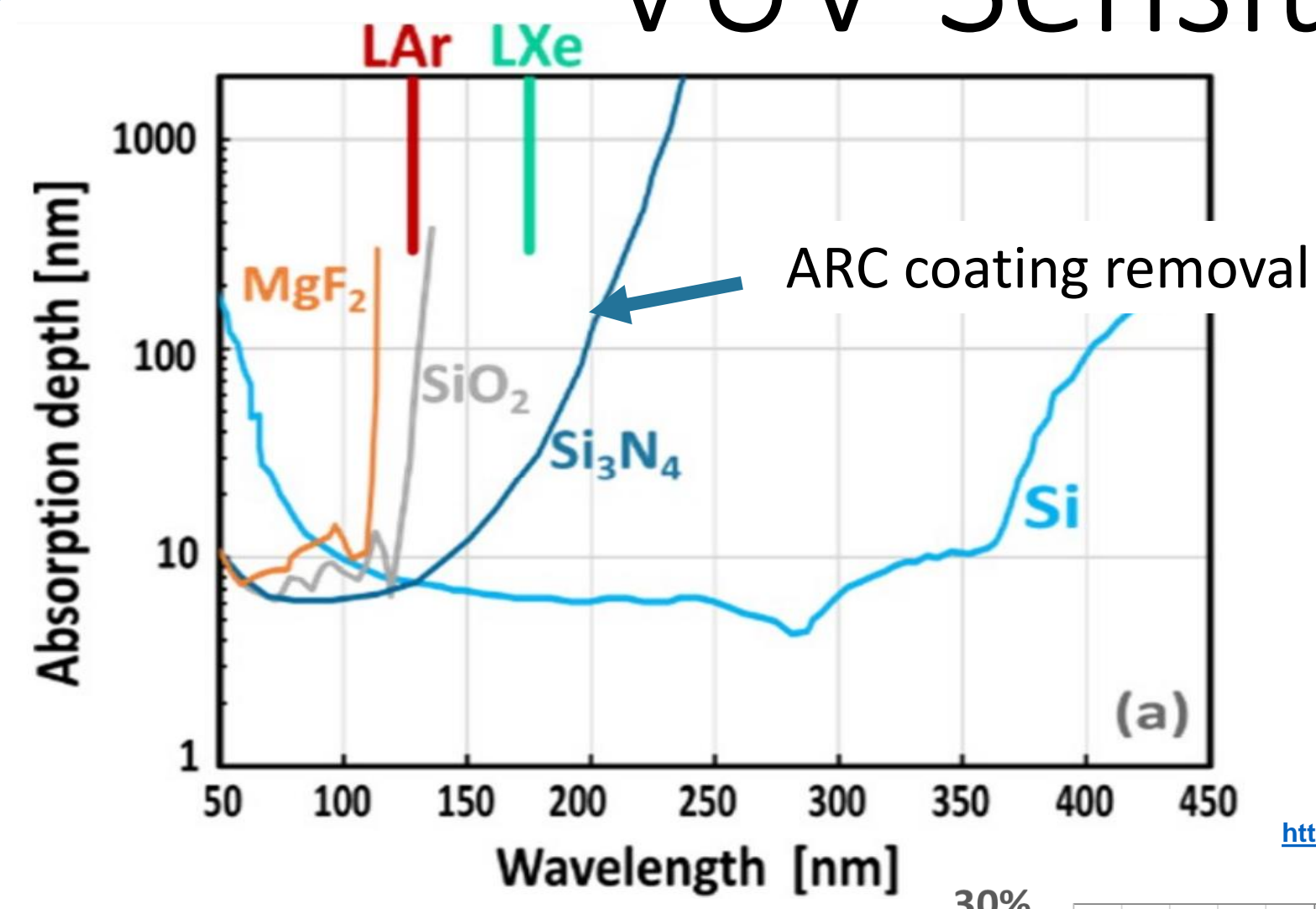


Rare Events Physics

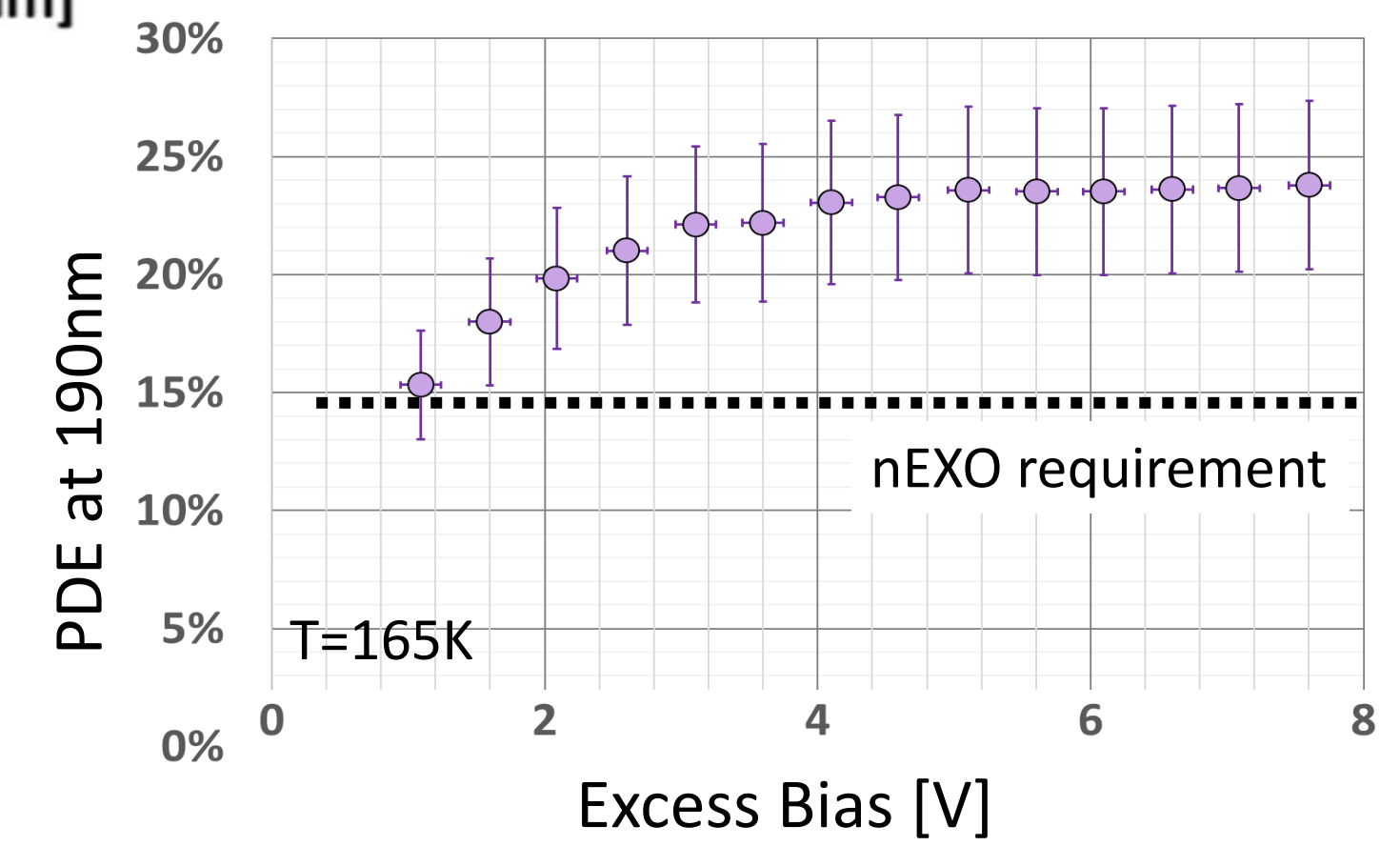
Liquid Xenon (LXe) based experiments:

- Good Absorber
- Chemically Inert
- High Yield Scintillator (178nm)
- Self-Transparent

VUV-Sensitive SiPM



Successful technology exceeding PDE requirements from experiments



Towards High Integration: TSV

Growing interest for:

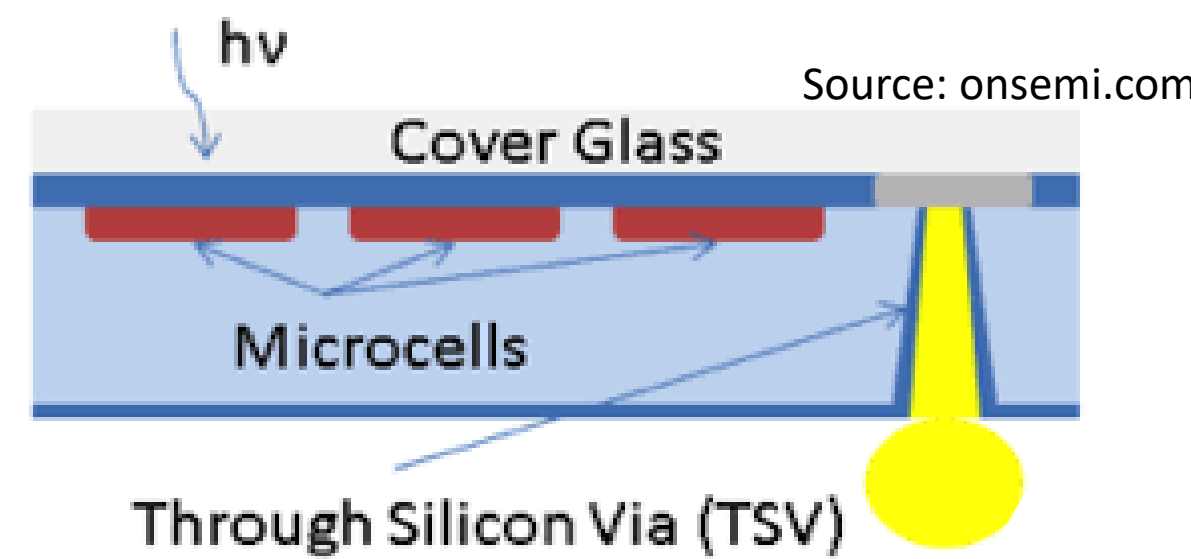
- High density array assembly with reduced non-active area
- Bypass wire-bond connection in application where it is potentially critical

TSV drawbacks for a SiPM

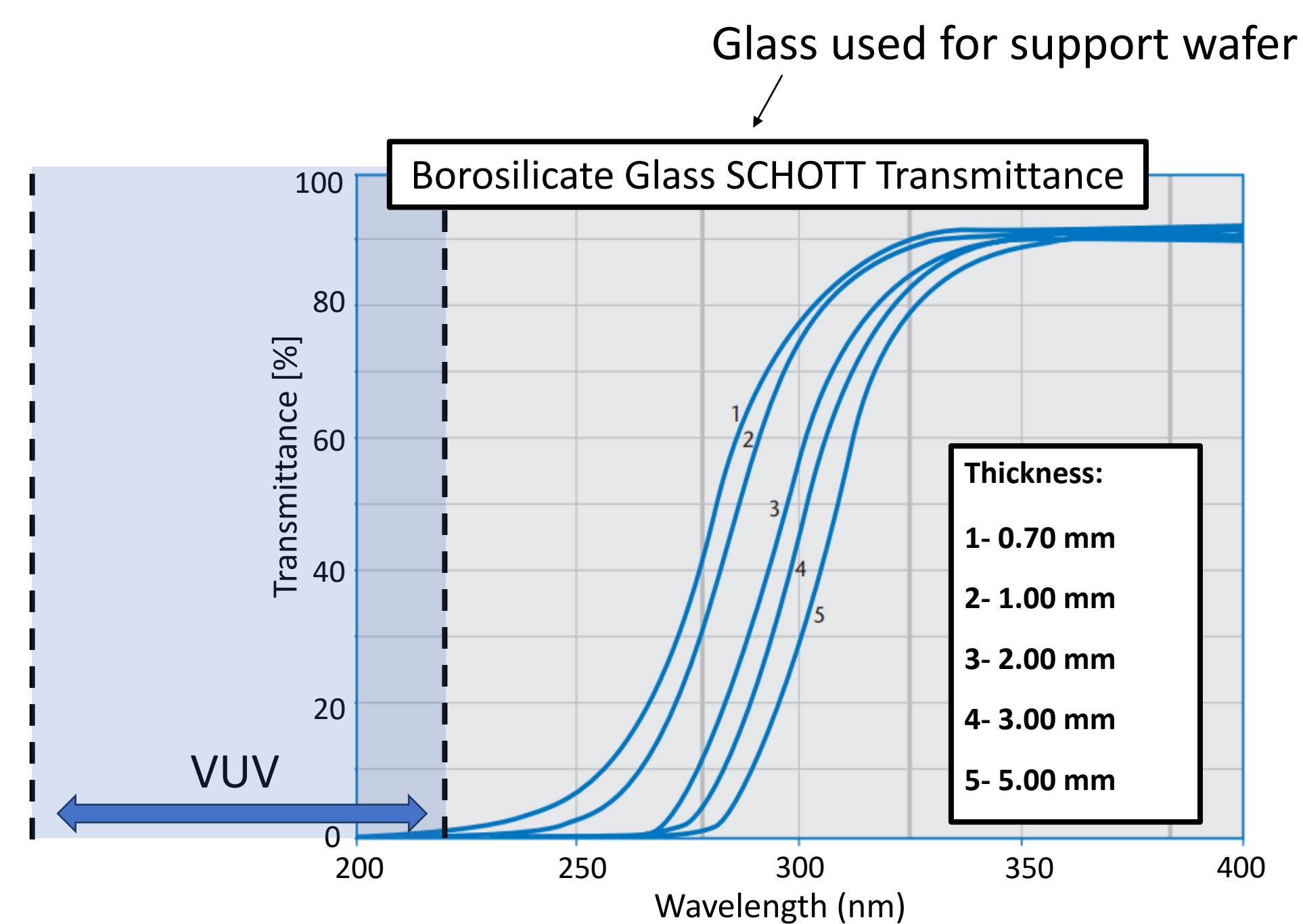
- Device attached to a glass support wafer
- Presence of a permanent bonding adhesive

Through Silicon Via (TSV)

Vertical electrical connection **that passes completely through a silicon wafer**, bringing the signal from the top (normally photosensitive side) to the bottom side of the device tier (interface with the front-end electronics)

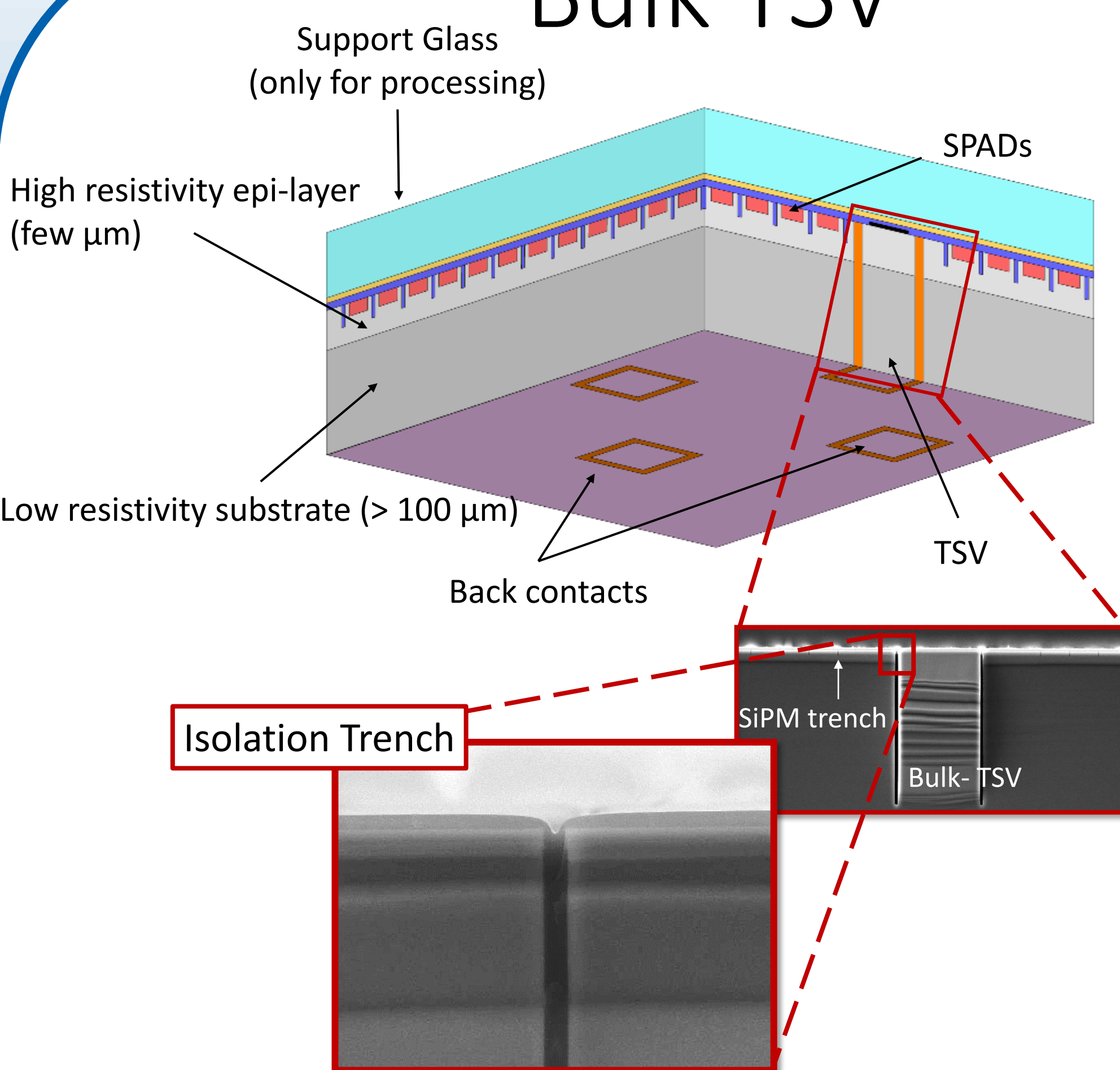


VUV Related Challenges for TSV



Glass can only be present as support structure during manufacturing and removed afterwards

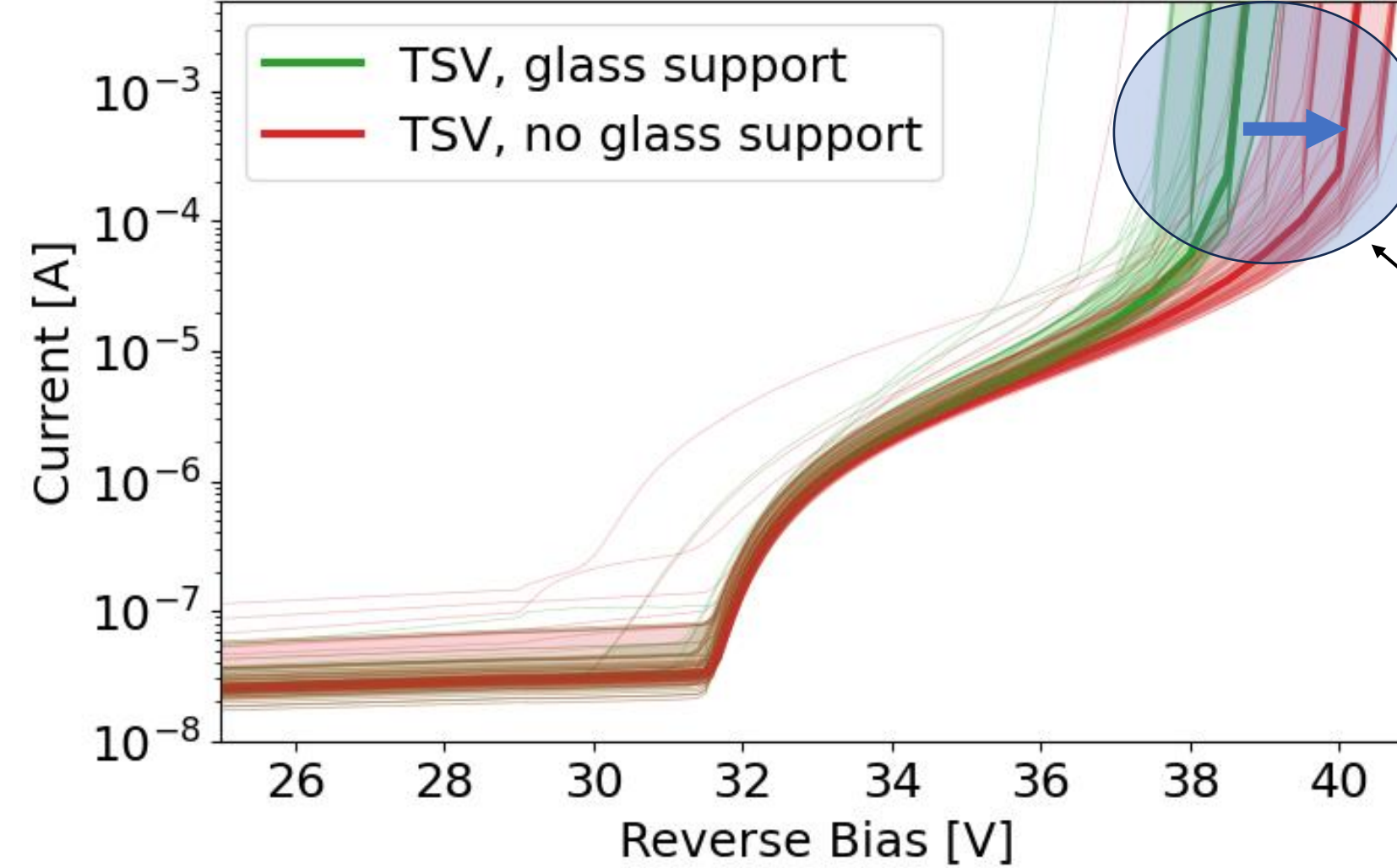
Bulk TSV



Main Features

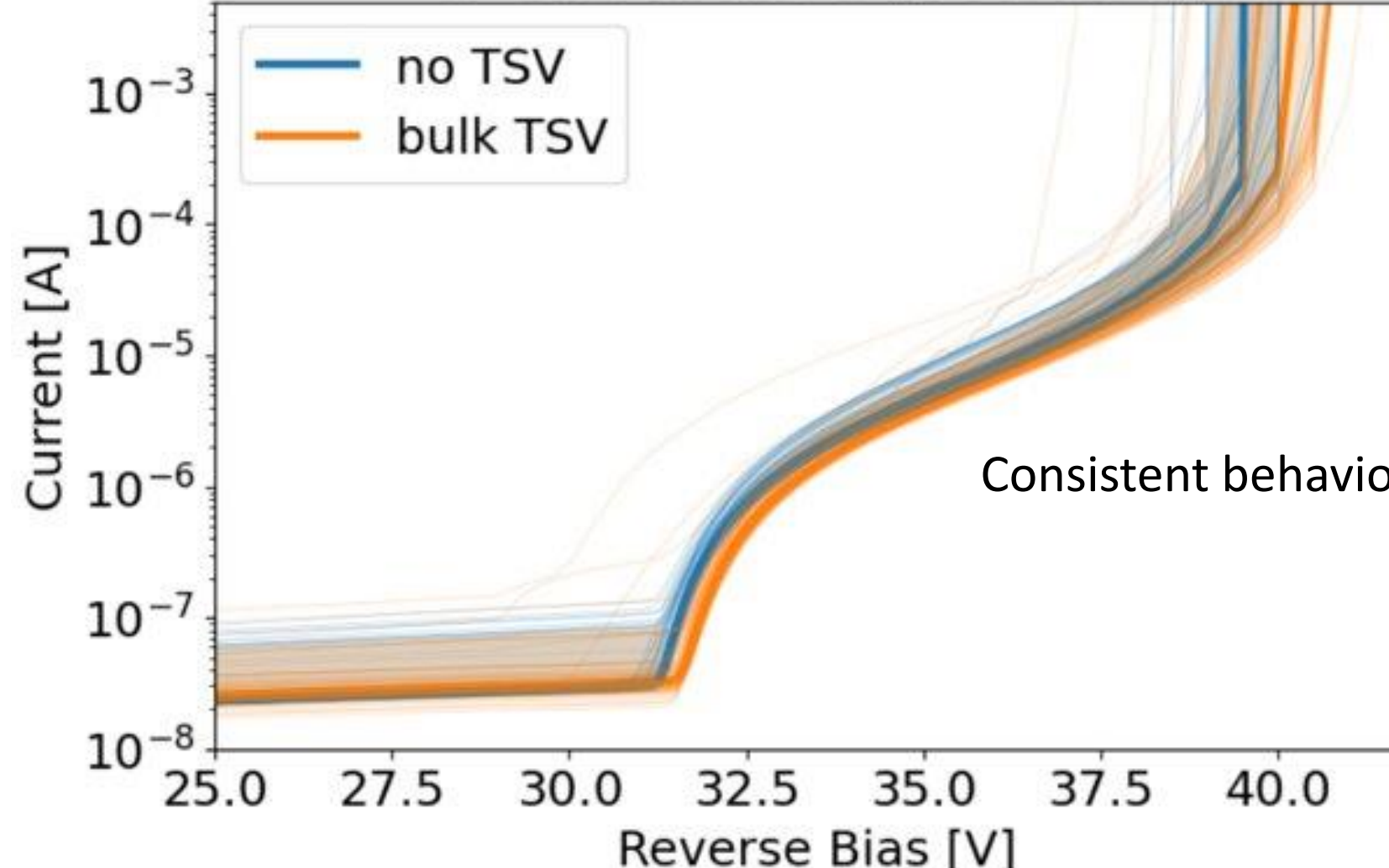
- No metallization, exploiting the substrate low resistivity
- Silicon TSV delimited by pass-through trenches.
- TSV density in the range 1-100 vias/mm²
- Low resistivity (~10 Ω) per via -> 1.5Ω/SiPM
- TSV width 10 μm – 100 μm depending on the final silicon thickness.
- TSV size/Si thickness aspect ratio of ~1

IV curves at RT for VUV-HD5



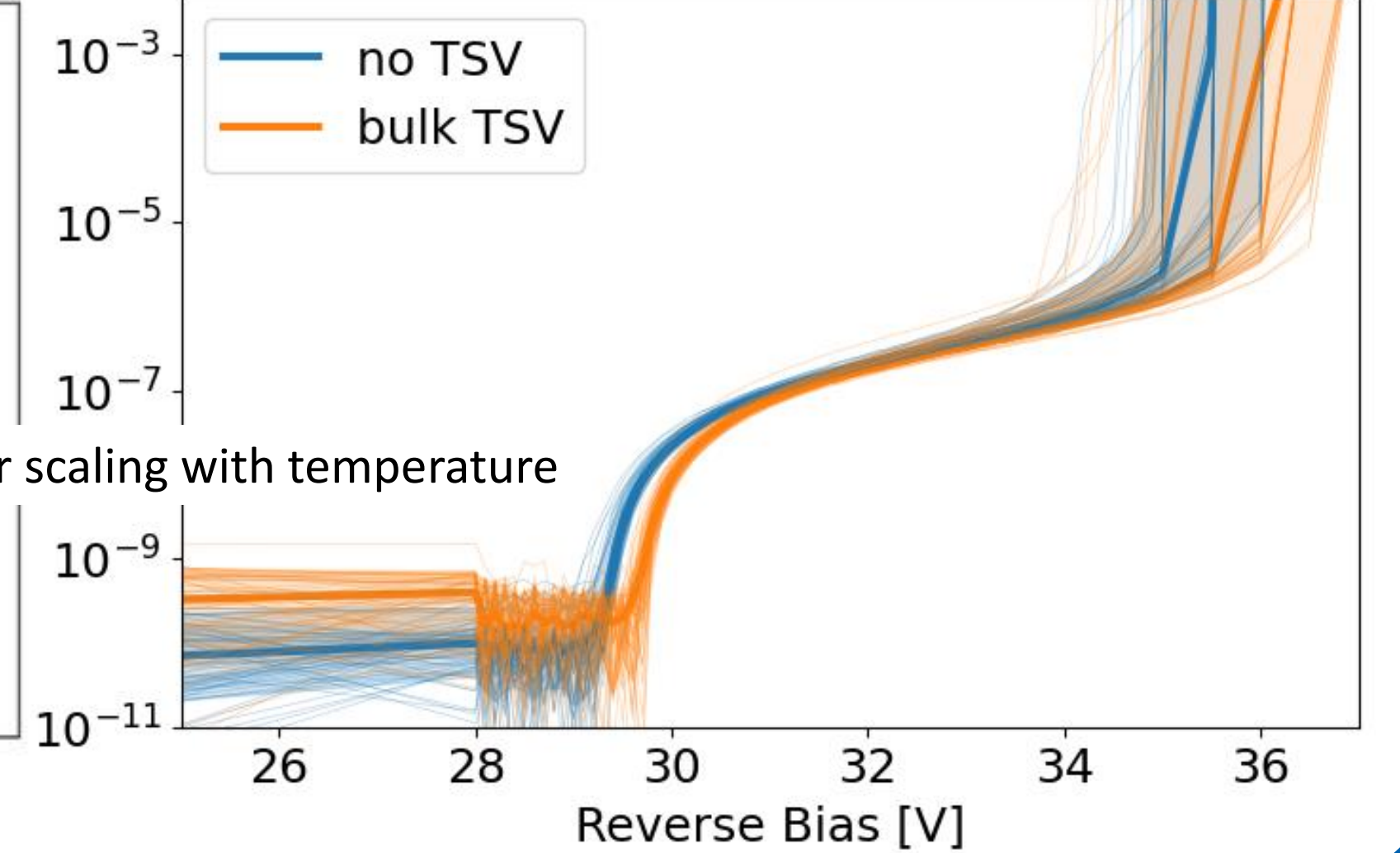
2nd divergence related to the correlated noise
Presence of the glass increases external cross-talk probability

IV curves at RT (VUV-HD5)

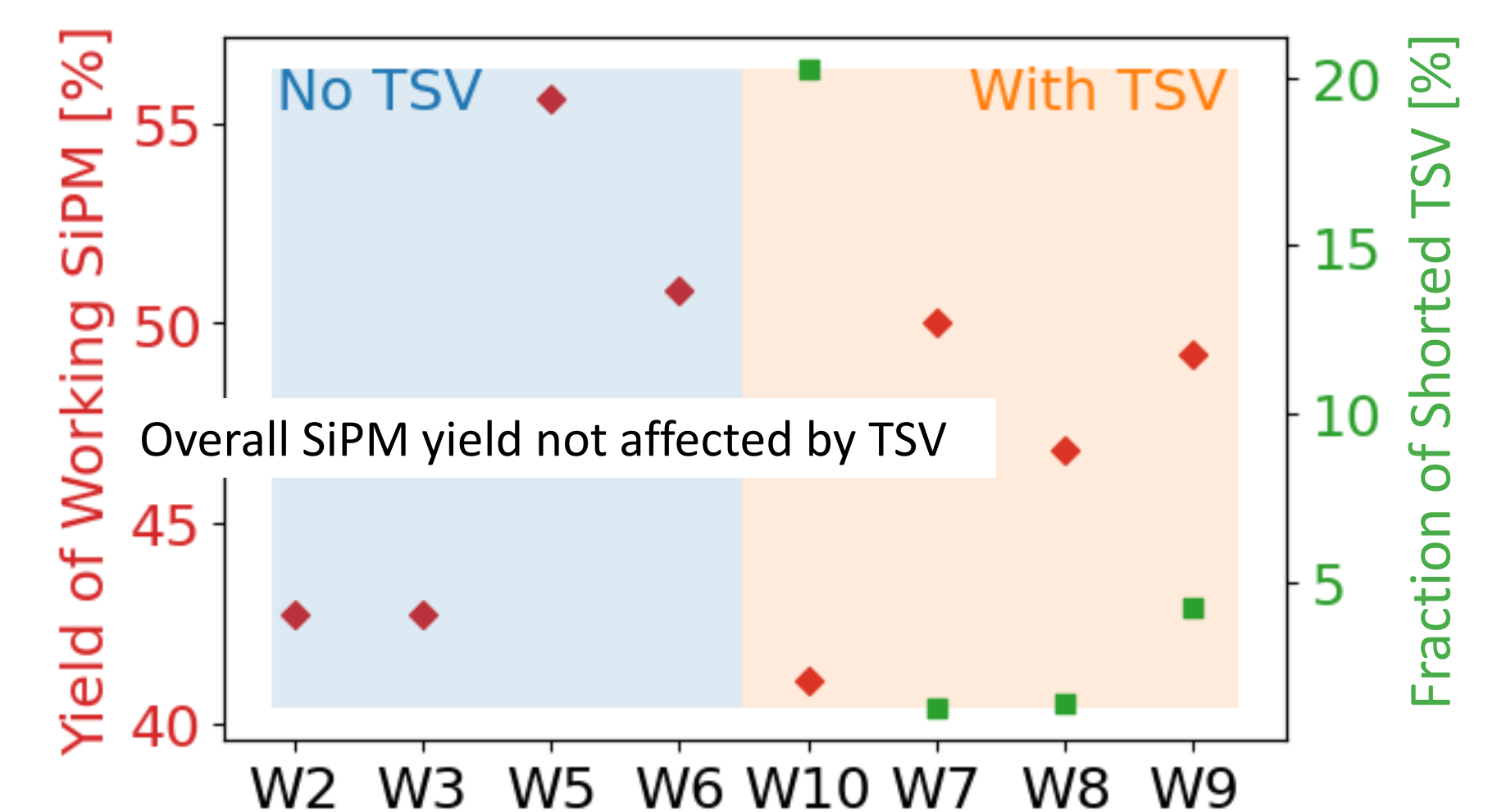


Consistent behavior scaling with temperature

IV curves at -40C (VUV-HD5)

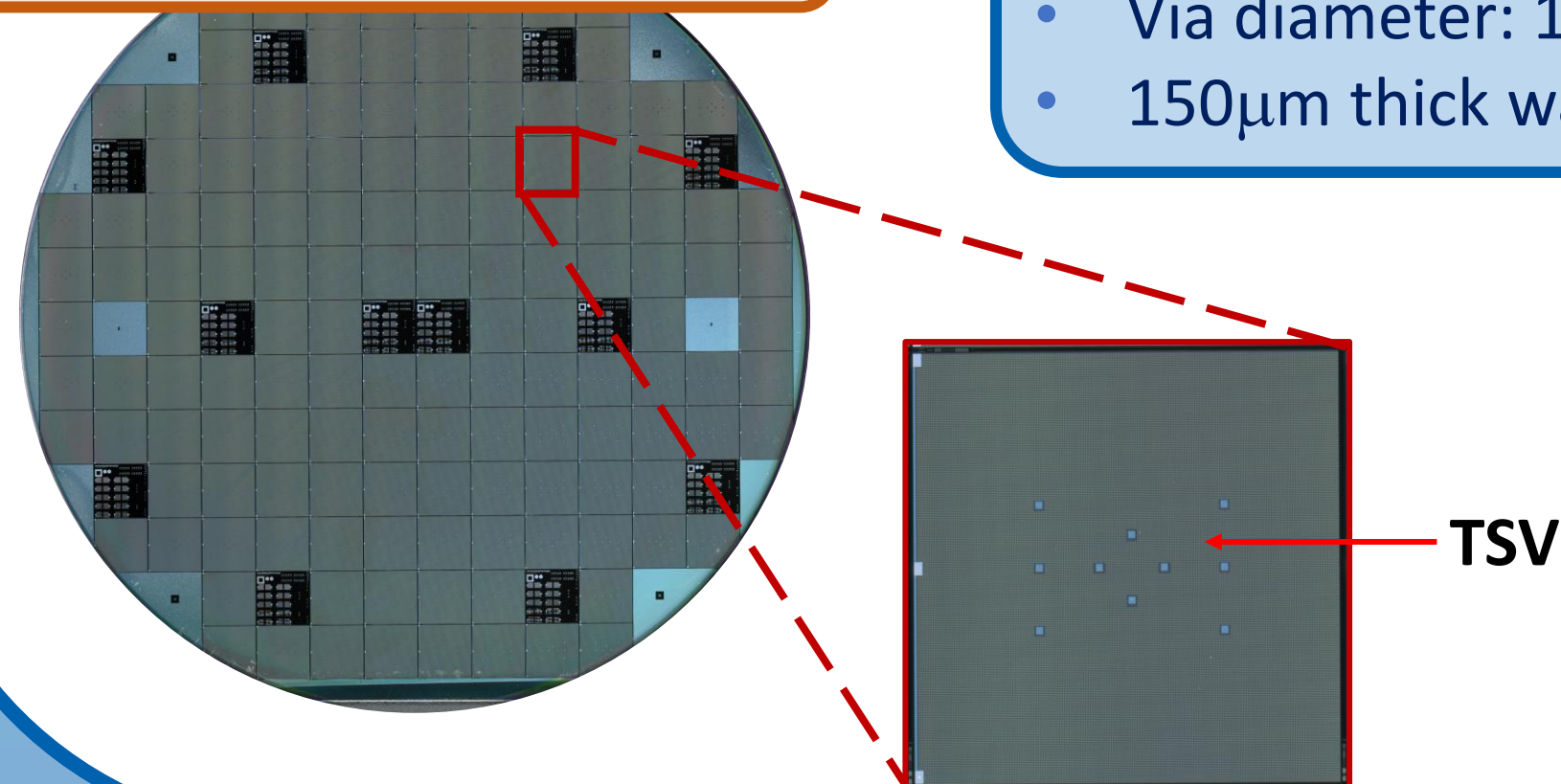


Results



Overall SiPM yield not affected by TSV

First produced wafer with TSV at FBK



- 10 x 10 mm² SiPM
- 10 TSV in parallel per SiPM
- Via diameter: 100 μm
- 150μm thick wafer

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